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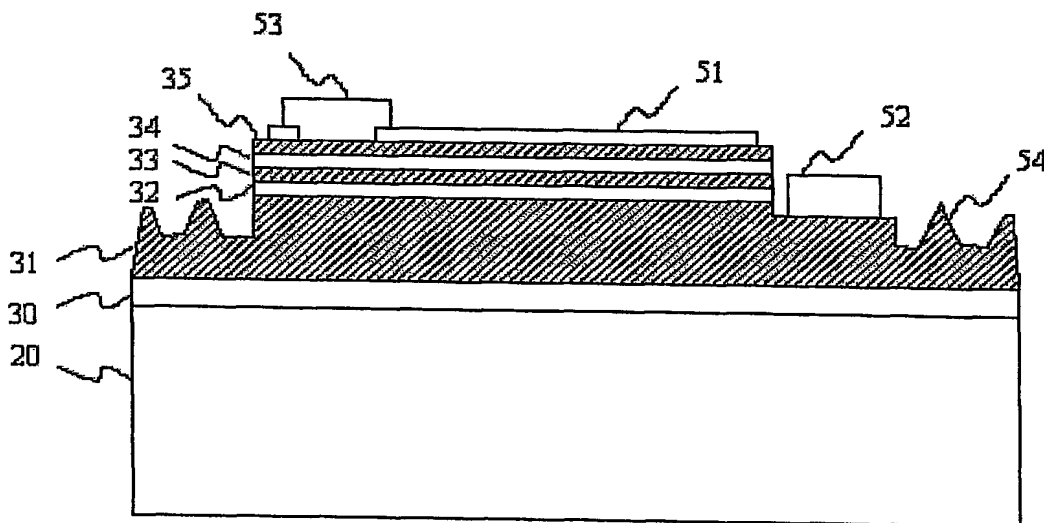
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(54) Title: **III-NITRIDE COMPOUND SEMICONDUCTOR LIGHT EMITTING DEVICE**



(57) Abstract: The present invention relates to a III-nitride semiconductor light-emitting device having high external quantum efficiency, provides a III-nitride compound semiconductor light-emitting device including an active layer generating light by recombination of electrons and holes and containing gallium and nitrogen, an n-type  $\text{Al}(x)\text{In}(y)\text{Ga}(1-x-y)\text{N}$  layer epitaxially grown before the active layer is grown, and an n-type electrode electrically contacting with the n-type  $\text{Al}(x)\text{In}(y)\text{Ga}(1-x-y)\text{N}$  layer, in which the device and a region for contact with the n-type electrode, and the surface of the region for scribing and breaking the device is roughened, thereby it is possible to increase external quantum efficiency of the light-emitting device.



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